

# HSK83

# Silicon Epitaxial Planar Diode for High Voltage Switching

REJ03G0191-0400Z (Previous: ADE-208-169C)

Rev.4.00

Mar.22.2004

#### **Features**

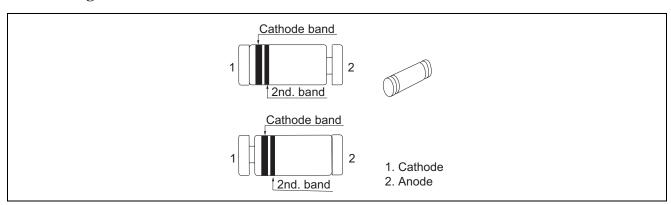
• High reverse voltage.  $(V_R = 250 \text{ V})$ 

• LLD package is suitable for high density surface mounting and high speed assembly.

## **Ordering Information**

Type No.	Cathode band	2nd band	Package Code
HSK83	White	Verdure	LLD

#### **Pin Arrangement**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit	
Peak reverse voltage	$V_{RM}$	300	V	
Reverse voltage	$V_R$	250	V	
Peak forward current	I <sub>FM</sub>	625	mA	
Non-Repetitive peak forward surge current	I <sub>FSM</sub> *1	1	Α	
Average rectified current	Io	150	mA	
Junction temperature	Tj	175	°C	
Storage temperature	Tstg	-65 to +175	°C	

Note: 1. Value at duration of 1s.

#### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	$V_{F}$	_	_	1.0	V	I <sub>F</sub> = 100 mA
Reverse current	I <sub>R1</sub>	_	_	0.1	μΑ	V <sub>R</sub> = 250 V
	I <sub>R2</sub>	_	_	100		V <sub>R</sub> = 300 V
Capacitance	С	_	1.5	_	pF	V <sub>R</sub> = 0 V, f = 1 MHz
Reverse recovery time	t <sub>rr</sub>	_	_	100	ns	$I_F = I_R = 30$ mA, $I_{rr} = 3$ mA, $R_L = 100$ $\Omega$

#### **Main Characteristics**

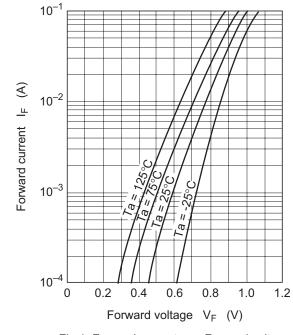


Fig.1 Forward current vs. Forward voltage

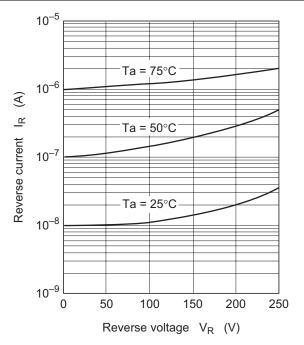
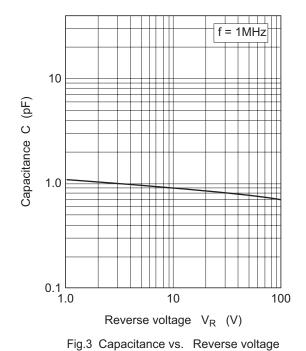
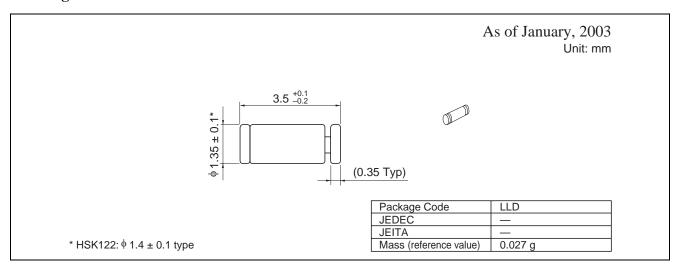


Fig.2 Reverse current vs. Reverse voltage



## **Package Dimensions**



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